

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3 and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 21:40
S1	3739	cmos and silicide and polysilicon with gate with electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 19:29
S2	1975	cmos and silicid\$3 same polysilicon with gate with electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/02/28 16:46
S3	1511	cmos and silicid\$3 with polysilicon with gate with electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/02/28 16:46
S4	79	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/02/28 16:47
S5	48	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 19:34
S6	245	(438/517).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 19:30
S7	956	(438/530).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 19:30

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S8	628	(438/682).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 19:32
S9	78	CABRAL-CYRIL-JR.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 19:33
S10	62	IEONG-MEIKEI .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 19:33
S11	9	KEDZIERSKI-JAKUB-t.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 19:33
S12	49	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 19:56
S13	2	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3 and (S9 or S10 or S11)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 19:36
S14	5	"6518113"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 19:37
S15	7	"6599831"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 19:42

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S16	506	(438/649).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/02 19:42
S17	26	cmos and silicid\$3 with polysilicon with gate with electrode and raised with source and polysilicon with dop\$3 and soi	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/03/02 21:40